TAIGITON

RB751S-40

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

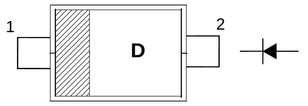
for high speed switching and detection applications

Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**D**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	30	mA
Peak Forward Surge Current (60 Hz, 1 Cycle)	I_{FSM}	200	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA	V_F	-	0.37	V
Reverse Current at V_R = 30 V	I_R	-	0.5	µA
Capacitance Between Terminals at V_R = 1 V, f = 1 MHz	C_T	2	-	pF

Note: ESD sensitive product handling required.

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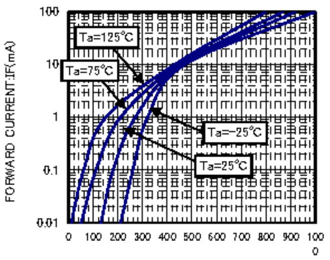
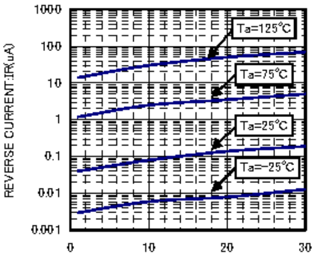
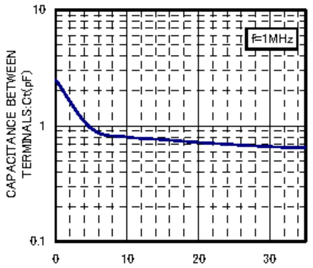


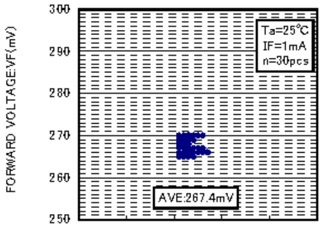
FORWARD VOLTAGE:VF(mV)
VF−IF CHARACTERISTICS
VF分布



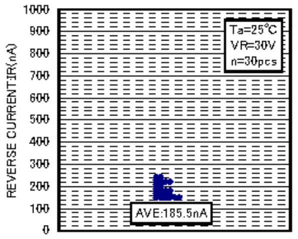
REVERSE VOLTAGE:VR(V)
VR−IR CHARACTERISTICS



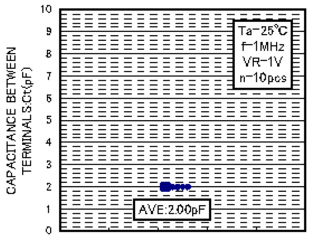
REVERSE VOLTAGE:VR(V)
VR−Ct CHARACTERISTICS



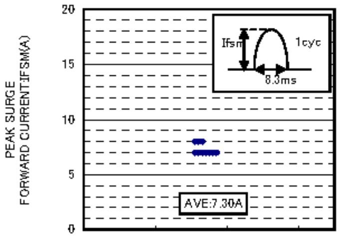
VF DIPERSION MAP



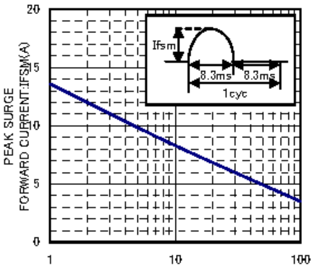
IR DISPERSION MAP



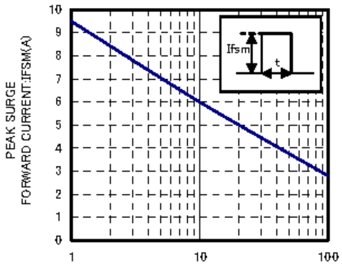
Ct DISPERSION MAP



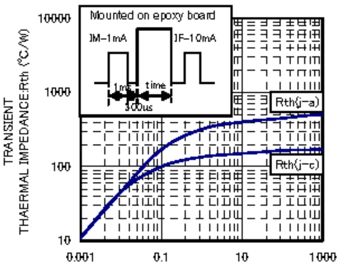
IFSM DISPERSION MAP



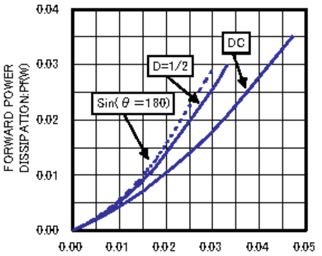
NUMBER OF CYCLES
IFSM−CYCLE CHARACTERISTICS



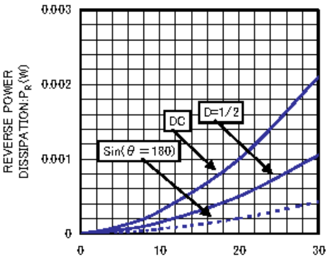
TIME:t(ms)
IFSM−t CHARACTERISTICS



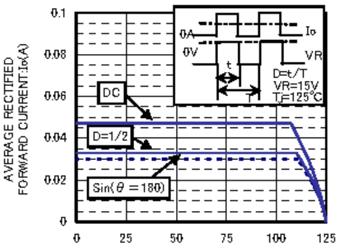
TIME:t(s)
Rth−t CHARACTERISTICS



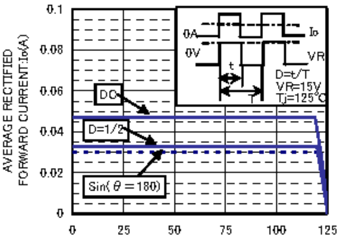
AVERAGE RECTIFIED
FORWARD CURRENT Io(A)
Io−Pf CHARACTERISTICS



REVERSE VOLTAGE:VR(V)
VR−P_R CHARACTERISTICS



AMBIENT TEMPERATURE:Ta(℃)
Derating Curve (Io−Ta)



CASE TEMPARATURE:Tc(℃)
Derating Curve (Io−Tc)